



Docket No.: MIT9944

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: McGill et al.

GROUP: Unknown

SERIAL NO: 10/632,442

EXAMINER: Unknown

FILED: 08/01/2003

FOR: YELLOW-GREEN EPITAXIAL TRANSPARENT SUBSTRATE-LEDs AND
LASERS BASED ON A STRAINED-INGAP QUANTUM WELL GROWN ON AN
INDIRECT BANDGAP SUBSTRATE

Mail DD
Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT

In compliance with 37 C.F.R. §§1.56, 1.97, and 1.98, Applicant submits copies of the documents listed on the attached Form PTO-1449.

The Commissioner is authorized to charge Deposit Order Account No. 19-0079 for any further fee that may be required.

Respectfully submitted,

Matthew E. Connors
Registration No. 33,298
Samuels, Gauthier & Stevens, LLP
225 Franklin Street, Suite 3300
Boston, Massachusetts 02110
Telephone: 617-426-9180, extension 112

I hereby certify that this paper (along with any paper referred to as being attached or enclosed) is being deposited with the United States Postal Service on the date shown below in an envelope, with sufficient postage as first class mail addressed to the Mail Stop DD, Commissioner of Patents, P.O. Box 1450 Alexandria, VA 22313-1450.

Emily G. Porell
09/09/03
Date

FORM PTO-1449 SAMUELS, GAUTHIER & STEVENS LLP
(Rev. 5/92) 225 Franklin Street, Boston, MA 02110
Telephone: (617) 426-9180

MIT.9944
ATTORNEY DOCKET NO.

10/632,442
SERIAL NO.

APPLICANT: McGill et al.

GROUP: Unknown

FILING DATE: August 1, 2003

EXAMINER: Unknown

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

SEP 12 2003

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AH						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
	AI	"Gas-Source Molecular Beam Epitaxial Growth, Characterization, and Light-Emitting diode application of $\text{In}_x\text{Ga}_{1-x}\text{P}$ on $\text{GaP}(100)$," Chin et al. <i>Applied Physics Letters</i> . May 1993. Vol. 62, No. 19.
	AJ	"Highly Strained $\text{In}_x\text{Ga}_{1-x}\text{P}/\text{GaP}$ Quantum Wells Grown on GaP and on an $\text{In}_{x/2}\text{Ga}_{1-x/2}\text{P}$ Buffer Layer by Gas-Source Molecular Beam Epitaxy," Bi et al. <i>Journal of Crystal Growth</i> . 1996. Vol. 165.
	AK	
	AL	
	AM	
	AN	

EXAMINER

DATE CONSIDERED

EXAMINER:

Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.